

AMENDMENTS TO THE CLAIMS

The following is a complete, marked-up listing of revised claims with a status identifier in parenthesis, underlined text indicating insertions, and strike through and/or double-bracketed text indicating deletions.

LISTING OF CLAIMS

1.-21. (Cancelled).

22. (Currently Amended) A capacitor of a semiconductor device, the capacitor comprising:

a lower electrode formed on a semiconductor substrate;

an AHO ((Al_xHf_{1-x})O_y) film formed on the lower electrode;

~~an~~ an upper electrode formed on the AHO ((Al_xHf_{1-x})O_y) film; and

a dielectric film having a dielectric constant that is higher than that of the AHO ((Al_xHf_{1-x})O_y) film between the upper electrode and the AHO ((Al_xHf_{1-x})O_y) film,

wherein the dielectric film is an HfO₂ layer, a ZrO₂ layer, or an STO layer, and

wherein the dielectric film is directly in contact with the upper electrode.

23. (Previously Presented) The capacitor of claim 22, further comprising:

an oxidation barrier film formed between the lower electrode and the AHO ((Al_xHf_{1-x})O_y) film.

24.-37. (Cancelled).

*** END CLAIM LISTING ***